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November 2013

FCP22N60N / FCPF22N60NT N-Channel SupreMOS® MOSFET

600 V, 22 A, 165 mΩ

Features

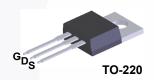
- $BV_{DSS} > 650 \text{ V } @ T_J = 150^{\circ}\text{C}$
- $R_{DS(on)}$ = 140 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 11 A
- Ultra Low Gate Charge (Typ. Q_q = 45 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 196.4 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

Application

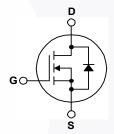
- LCD/LED/PDP TV
- Lighting
- · Solar Inverter
- · AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FCP22N60N	FCPF22N60NT	Unit
V_{DSS}	Drain to Source Voltage			6	V	
V_{GSS}	Gate to Source Voltage			±	:45	V
	Drain Current	- Continuous (T _C = 25°C)		22 22*		Α
I _D	Drain Current - Continuous (T _C = 100°C)		13.8	13.8*	A	
I _{DM}	Drain Current - Pulsed (Note 1)) 66 66*		Α
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			6	mJ	
I _{AR}	Avalanche Current (Note 1)			7.3		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)			2.75		mJ
dv/dt	MOSFET dv/dt			100		V/ns
uv/ut	Peak Diode Recovery dv/d	it	(Note 3)	3) 20		V/115
D	Power Dissipation (T _C = 25°C)		205	39	W	
P_{D}	- Derate Above 25°C		1.64	0.31	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150		οС
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds 300			°С		

^{*}Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCP22N60N	FCPF22N60NT	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.61	3.2	°C/W
$R_{\theta,JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	-0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP22N60N	FCP22N60N	TO-220	Tube	N/A	N/A	50 units
FCPF22N60NT	FCPF22N60NT	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter		Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics						
D\/	Drain to Source Breakdown Voltage		$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$	600	-	-	V
BV_{DSS}	Drain to Source Breakdown Voltage		$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 150^{\circ}\text{C}$	650	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient		I _D = 1 mA, Referenced to 25°C	-	0.68	-	V/°C
1	Zana Cata Valta da Dunia Comunat		V _{DS} = 480 V, V _{GS} = 0 V	-	-	10	^
IDSS	Zero Gate Voltage Drain Current		V _{DS} = 480 V, T _J = 125°C	-	-	100	μΑ
I _{GSS}	Gate to Body Leakage Current		V _{GS} = ±45 V, V _{DS} = 0 V	-	-	±100	nA
O Ob	-4						
On Charac	cteristics						

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.0	3.0	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 11 A	-	0.140	0.165	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 11 A	-	22	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	400 1/ 1/ 0 1/	-	1950	-	pF
C _{oss}	Output Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	- \	75.9	-	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12	- \	3	-	pF
Coss	Output Capacitance	$V_{DS} = 380 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	43.2	-	pF
C _{oss(eff.)}	Effective Output Capacitance	$V_{DS} = 0 V \text{ to } 480 V, V_{GS} = 0 V$	-	196.4	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380 V, I _D = 11 A,	-	45	-	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	8.7	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	14.5	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	16.9	-	ns
t _r	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_D = 11 \text{ A}$	-	16.7	-	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 4.7 Ω	-	49	-	ns
t _f	Turn-Off Fall Time	(Note 4)	-	4	-	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode	Maximum Continuous Drain to Source Diode Forward Current		-	22	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	66	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 11 A	-	_	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 11 A	-	350	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	6	-	μС

Notes:

- 1. Repetitive rating: pulse width-limited by maximum junction temperature.
- 2. I_{AS} = 7.3 A, R_{G} = 25 Ω , starting T_{J} = 25°C.
- 3. I $_{SD} \leq$ 22 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ 380 V, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics *Notes: 1. 250µs Pulse Test 2. T_C = 25°C b, Drain Current[A] V_{GS} = 15.0 V 10.0 V 8.0 V 7.0 V 6.0 V 5.0 V 4.0 V 0.1 0.3 10 V_{DS},Drain-Source Voltage[V]

Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

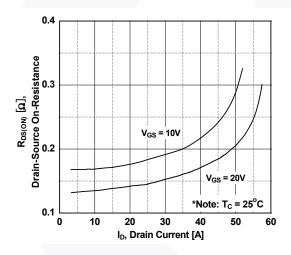


Figure 5. Capacitance Characteristics

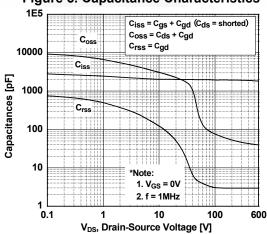


Figure 2. Transfer Characteristics

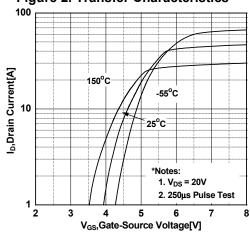


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

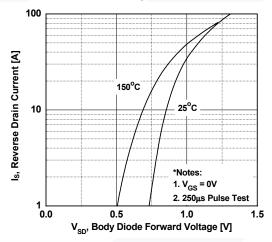
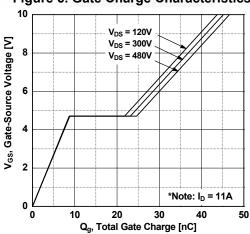


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

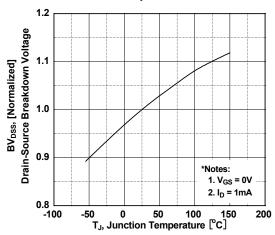


Figure 9. Maximum Safe Operating Area for FCP22N60N

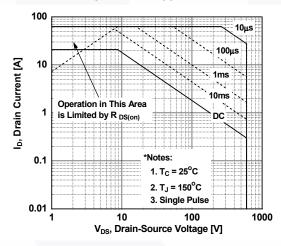


Figure 8. On-Resistance Variation vs. Temperature

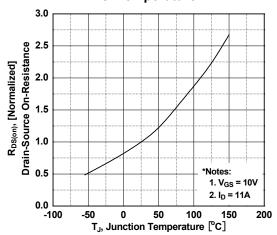


Figure 10. Maximum Safe Operating Area for FCPF22N60NT

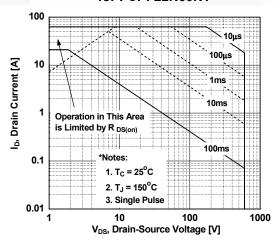
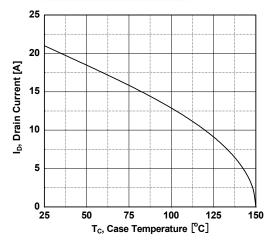


Figure 11. Maximum Drain Current vs.Case Temperature



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve for FCP22N60N

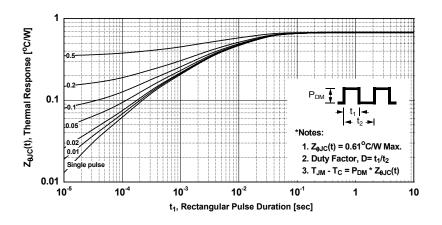
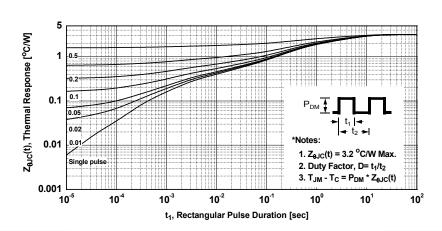


Figure 13. Transient Thermal Response Curve for FCPF22N60NT



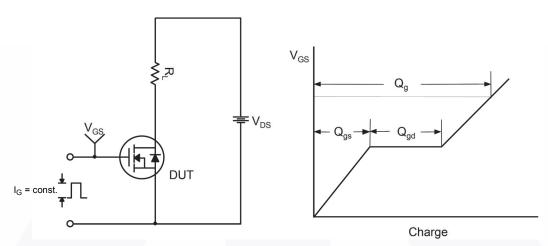


Figure 14. Gate Charge Test Circuit & Waveform

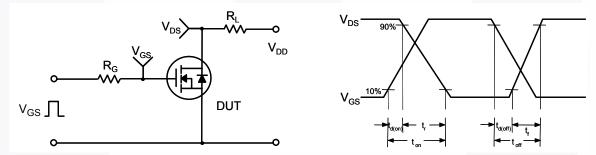


Figure 15. Resistive Switching Test Circuit & Waveforms

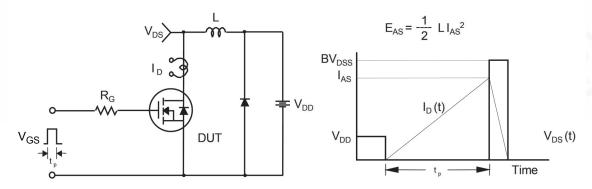


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

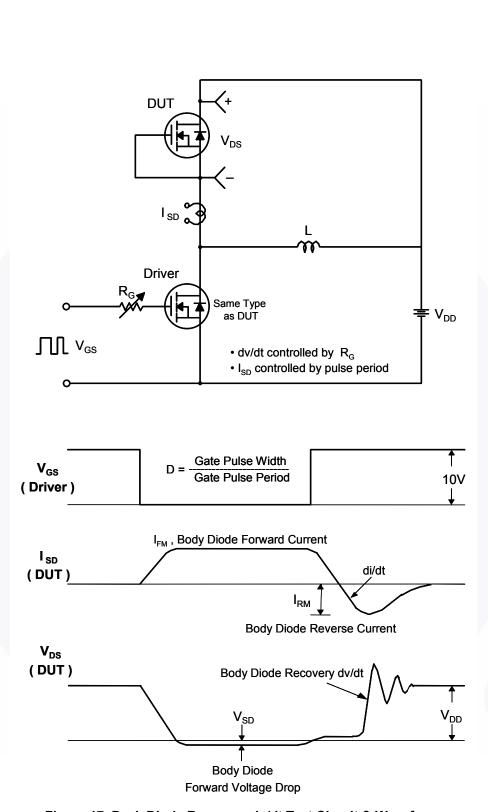


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

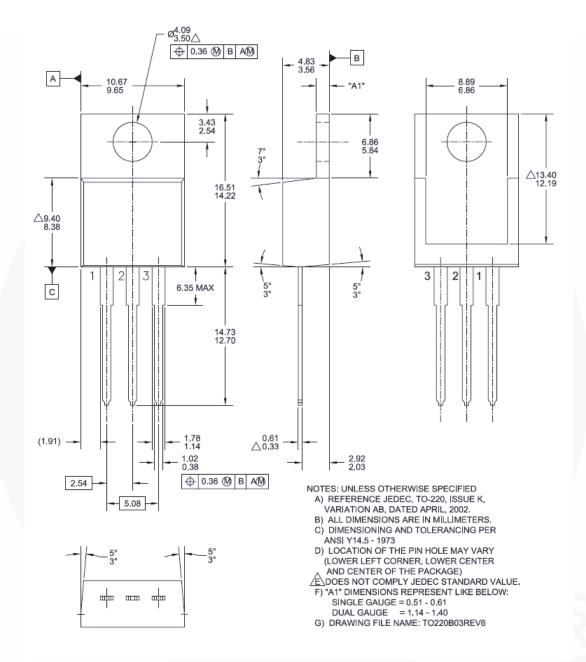


Figure 18. TO-220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

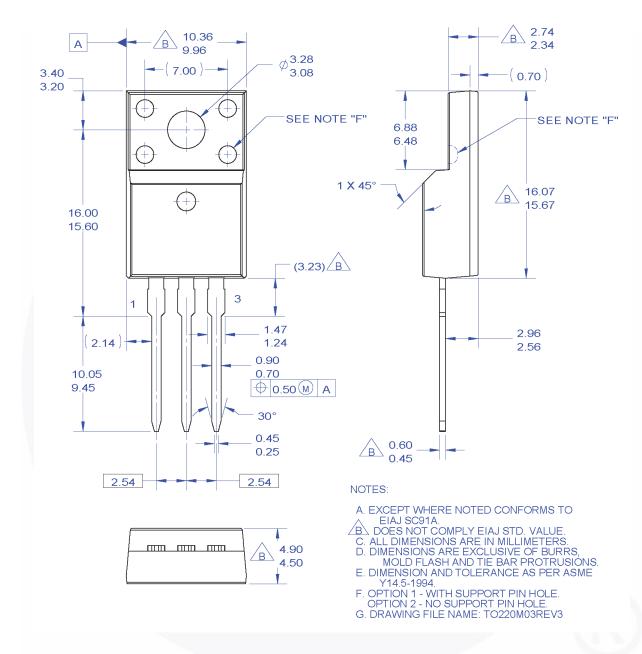


Figure 19. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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